

Michael Jetter

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187
papers

2,689
citations

28
h-index

42
g-index

229
ext. papers

3,218
ext. citations

3.5
avg, IF

4.91
L-index

#	Paper	IF	Citations
187	Visible-to-telecom quantum frequency conversion of light from a single quantum emitter. <i>Physical Review Letters</i> , 2012 , 109, 147404	7.4	159
186	Cascaded single-photon emission from the Mollow triplet sidebands of a quantum dot. <i>Nature Photonics</i> , 2012 , 6, 238-242	33.9	98
185	Detuning-dependent Mollow triplet of a coherently-driven single quantum dot. <i>Optics Express</i> , 2013 , 21, 4382-95	3.3	87
184	Band-gap measurements of direct and indirect semiconductors using monochromated electrons. <i>Physical Review B</i> , 2007 , 75,	3.3	82
183	Differential phase contrast 2.0--opening new "fields" for an established technique. <i>Ultramicroscopy</i> , 2012 , 117, 7-14	3.1	72
182	Single-photon emission at 1.55 μm from MOVPE-grown InAs quantum dots on InGaAs/GaAs metamorphic buffers. <i>Applied Physics Letters</i> , 2017 , 111, 033102	3.4	63
181	Quantum key distribution using quantum dot single-photon emitting diodes in the red and near infrared spectral range. <i>New Journal of Physics</i> , 2012 , 14, 083001	2.9	63
180	Ultra-sensitive mid-infrared evanescent field sensors combining thin-film strip waveguides with quantum cascade lasers. <i>Analyst, The</i> , 2012 , 137, 2322-7	5	60
179	Optical and structural properties of InP quantum dots embedded in $(\text{Al}_x\text{Ga}_{1-x})_{0.51}\text{In}_{0.49}\text{P}$. <i>Physical Review B</i> , 2009 , 79,	3.3	56
178	Three-dimensional GaN for semipolar light emitters. <i>Physica Status Solidi (B): Basic Research</i> , 2011 , 248, 549-560	1.3	55
177	Phonon-assisted incoherent excitation of a quantum dot and its emission properties. <i>Physical Review B</i> , 2012 , 86,	3.3	52
176	Two-photon interference in the telecom C-band after frequency conversion of photons from remote quantum emitters. <i>Nature Nanotechnology</i> , 2019 , 14, 23-26	28.7	50
175	Electrically driven quantum dot single-photon source at 2 GHz excitation repetition rate with ultra-low emission time jitter. <i>Applied Physics Letters</i> , 2013 , 102, 011126	3.4	45
174	Polarization-entangled photons from an InGaAs-based quantum dot emitting in the telecom C-band. <i>Applied Physics Letters</i> , 2017 , 111, 133106	3.4	43
173	Combining in-situ lithography with 3D printed solid immersion lenses for single quantum dot spectroscopy. <i>Scientific Reports</i> , 2017 , 7, 39916	4.9	42
172	Fully On-Chip Single-Photon Hanbury-Brown and Twiss Experiment on a Monolithic Semiconductor-Superconductor Platform. <i>Nano Letters</i> , 2018 , 18, 6892-6897	11.5	42
171	InP/AlGaInP quantum dot laser emitting at 638 nm. <i>Journal of Crystal Growth</i> , 2011 , 315, 123-126	1.6	41

170	Near-red emission from site-controlled pyramidal InGaN quantum dots. <i>Applied Physics Letters</i> , 2005 , 87, 163121	3-4	38
169	Electrically pumped single-photon emission in the visible spectral range up to 80 K. <i>Optics Express</i> , 2008 , 16, 12771-6	3-3	37
168	Influence of the dark exciton state on the optical and quantum optical properties of single quantum dots. <i>Physical Review Letters</i> , 2008 , 101, 146402	7-4	36
167	Mid-Infrared Spectroscopy Platform Based on GaAs/AlGaAs Thin-Film Waveguides and Quantum Cascade Lasers. <i>Analytical Chemistry</i> , 2016 , 88, 2558-62	7-8	35
166	Reducing vortex losses in superconducting microwave resonators with microsphere patterned antidot arrays. <i>Applied Physics Letters</i> , 2012 , 100, 012601	3-4	33
165	Metal-organic vapor-phase epitaxy-grown ultra-low density InGaAs/GaAs quantum dots exhibiting cascaded single-photon emission at 1.3 μm . <i>Applied Physics Letters</i> , 2015 , 106, 122105	3-4	32
164	Monolithic on-chip integration of semiconductor waveguides, beamsplitters and single-photon sources. <i>Journal Physics D: Applied Physics</i> , 2015 , 48, 085101	3	31
163	Semiconductor membrane external-cavity surface-emitting laser (MECSEL). <i>Optica</i> , 2016 , 3, 1506	8-6	31
162	Electronic shell structure and carrier dynamics of high aspect ratio InP single quantum dots. <i>Physical Review B</i> , 2007 , 75,	3-3	30
161	Semiconductor Quantum Dots for Integrated Quantum Photonics. <i>Advanced Quantum Technologies</i> , 2019 , 2, 1900020	4-3	29
160	Mode-locked red-emitting semiconductor disk laser with sub-250 fs pulses. <i>Applied Physics Letters</i> , 2013 , 103, 242101	3-4	28
159	Structural and optical properties of InAs/(In)GaAs/GaAs quantum dots with single-photon emission in the telecom C-band up to 77 K. <i>Physical Review B</i> , 2018 , 98,	3-3	28
158	On-chip beamsplitter operation on single photons from quasi-resonantly excited quantum dots embedded in GaAs rib waveguides. <i>Applied Physics Letters</i> , 2015 , 107, 021101	3-4	27
157	Generation, guiding and splitting of triggered single photons from a resonantly excited quantum dot in a photonic circuit. <i>Optics Express</i> , 2016 , 24, 3089-94	3-3	27
156	Simultaneous Faraday filtering of the Mollow triplet sidebands with the Cs-D clock transition. <i>Nature Communications</i> , 2016 , 7, 13632	17-4	27
155	Quantitative measurements of internal electric fields with differential phase contrast microscopy on InGaN/GaN quantum well structures. <i>Physica Status Solidi (B): Basic Research</i> , 2016 , 253, 140-144	1-3	26
154	Deterministic integration and optical characterization of telecom O-band quantum dots embedded into wet-chemically etched Gaussian-shaped microlenses. <i>Applied Physics Letters</i> , 2018 , 113, 032103	3-4	24
153	High-power InP quantum dot based semiconductor disk laser exceeding 1.3 W. <i>Applied Physics Letters</i> , 2013 , 102, 092101	3-4	24

152	Lasing properties of InP/(Ga _{0.51} In _{0.49})P quantum dots in microdisk cavities. <i>Physical Review B</i> , 2011 , 83,	3.3	24
151	Single-photon emission from a type-B InP/GaInP quantum dot. <i>Journal of Applied Physics</i> , 2005 , 98, 093522-5	2.5	24
150	InAs quantum dots grown on metamorphic buffers as non-classical light sources at telecom C-band: a review. <i>Semiconductor Science and Technology</i> , 2019 , 34, 053001	1.8	23
149	Triggered single-photon emission from electrically excited quantum dots in the red spectral range. <i>Applied Physics Letters</i> , 2010 , 97, 143513	3.4	22
148	Red to green photoluminescence of InP-quantum dots in InP. <i>Journal of Crystal Growth</i> , 2007 , 298, 595-598	5.8	22
147	Two-photon interference in an atom-quantum dot hybrid system. <i>Optica</i> , 2018 , 5, 367	8.6	21
146	Coherence and indistinguishability of highly pure single photons from non-resonantly and resonantly excited telecom C-band quantum dots. <i>Applied Physics Letters</i> , 2019 , 115, 023103	3.4	21
145	Short wavelength red-emitting AlGaInP-VECSEL exceeds 1.2 W continuous-wave output power. <i>Applied Physics B: Lasers and Optics</i> , 2011 , 102, 789-794	1.9	21
144	Deterministic fabrication of circular Bragg gratings coupled to single quantum emitters via the combination of in-situ optical lithography and electron-beam lithography. <i>Journal of Applied Physics</i> , 2019 , 125, 045701	2.5	20
143	Room-temperature lasing of electrically pumped red-emitting InP/(Al _{0.20} Ga _{0.80}) _{0.51} In _{0.49} P quantum dots embedded in a vertical microcavity. <i>Applied Physics Letters</i> , 2009 , 95, 131107	3.4	20
142	Structural and emission properties of InGaAs/GaAs quantum dots emitting at 1.3 μ m. <i>Applied Physics Letters</i> , 2014 , 105, 152102	3.4	19
141	Electric-Field Tuning of Spin-Dependent Exciton-Exciton Interactions in Coupled Quantum Wells. <i>Physical Review Letters</i> , 1999 , 83, 2433-2436	7.4	19
140	Low-noise quantum frequency down-conversion of indistinguishable photons. <i>Optics Express</i> , 2016 , 24, 22250-60	3.3	19
139	Spectroscopy of the D1 transition of cesium by dressed-state resonance fluorescence from a single (In,Ga)As/GaAs quantum dot. <i>Physical Review B</i> , 2014 , 90,	3.3	18
138	Wavelength tunable ultraviolet laser emission via intra-cavity frequency doubling of an AlGaInP vertical external-cavity surface-emitting laser down to 328 nm. <i>Applied Physics Letters</i> , 2011 , 99, 261101	3.4	18
137	Time- and locally resolved photoluminescence of semipolar GaInN/GaN facet light emitting diodes. <i>Applied Physics Letters</i> , 2007 , 90, 171123	3.4	18
136	Neutral and charged biexciton-exciton cascade in near-telecom-wavelength quantum dots. <i>Physical Review B</i> , 2016 , 94,	3.3	17
135	2.5 W continuous wave output at 665 nm from a multipass and quantum-well-pumped AlGaInP vertical-external-cavity surface-emitting laser. <i>Optics Letters</i> , 2016 , 41, 1245-8	3	16

134	High wavelength tunability of InGaN quantum wells grown on semipolar GaN pyramid facets. <i>Physica Status Solidi (B): Basic Research</i> , 2011 , 248, 605-610	1.3	16
133	Triggered single-photon emission in the red spectral range from optically excited InP/(Al,Ga)InP quantum dots embedded in micropillars up to 100 K. <i>Journal of Applied Physics</i> , 2011 , 110, 063108	2.5	16
132	DBR-free semiconductor disc laser on SiC heatspreader emitting 10.1 W at 1007nm. <i>Electronics Letters</i> , 2017 , 53, 1537-1539	1.1	15
131	High optical output power in the UVA range of a frequency-doubled, strain-compensated AlGaInP-VECSEL. <i>Applied Physics Express</i> , 2014 , 7, 092705	2.4	15
130	Intra-cavity frequency-doubled mode-locked semiconductor disk laser at 325 nm. <i>Optics Express</i> , 2015 , 23, 19947-53	3.3	14
129	Mollow quintuplets from coherently excited quantum dots. <i>Optics Letters</i> , 2013 , 38, 1691-3	3	14
128	Nonresonant tunneling in single asymmetric pairs of vertically stacked InP quantum dots. <i>Physical Review B</i> , 2007 , 76,	3.3	14
127	Temperature-dependent properties of single long-wavelength InGaAs quantum dots embedded in a strain reducing layer. <i>Journal of Applied Physics</i> , 2017 , 121, 184302	2.5	13
126	Enhanced efficiency of AlGaInP disk laser by in-well pumping. <i>Optics Express</i> , 2015 , 23, 2472-86	3.3	13
125	Single-photon and photon pair emission from MOVPE-grown In(Ga)As quantum dots: shifting the emission wavelength from 1.0 to 1.3 μ m. <i>Applied Physics B: Lasers and Optics</i> , 2016 , 122, 1	1.9	13
124	All quantum dot mode-locked semiconductor disk laser emitting at 655 nm. <i>Applied Physics Letters</i> , 2014 , 105, 082107	3.4	13
123	Postselected indistinguishable single-photon emission from the Mollow triplet sidebands of a resonantly excited quantum dot. <i>Physical Review B</i> , 2013 , 87,	3.3	13
122	Low-density InP quantum dots embedded in Ga _{0.51} In _{0.49} P with high optical quality realized by a strain inducing layer. <i>Applied Physics Letters</i> , 2010 , 97, 063107	3.4	13
121	Red single-photon emission from an InP/AlGaInP quantum dot embedded in a planar monolithic microcavity. <i>Applied Physics Letters</i> , 2008 , 92, 071105	3.4	13
120	Characterisation of quaternary AlInGaN thick layers and quantum wells grown by MOVPE. <i>Journal of Crystal Growth</i> , 2004 , 272, 386-392	1.6	13
119	Low density MOVPE grown InGaAs QDs exhibiting ultra-narrow single exciton linewidths. <i>Nanotechnology</i> , 2010 , 21, 125606	3.4	12
118	Low Threshold InP/AlGaInP Quantum Dot In-Plane Laser Emitting at 638 nm. <i>Applied Physics Express</i> , 2009 , 2, 112501	2.4	12
117	Polarization fine structure and enhanced single-photon emission of self-assembled lateral InGaAs quantum dot molecules embedded in a planar microcavity. <i>Journal of Applied Physics</i> , 2009 , 105, 122408	2.5	12

116	Selective growth of GaInN quantum dot structures. <i>Journal of Crystal Growth</i> , 2004 , 272, 204-210	1.6	12
115	Red VCSEL for high-temperature applications. <i>Journal of Crystal Growth</i> , 2004 , 272, 549-554	1.6	12
114	Microcavity-enhanced Kerr nonlinearity in a vertical-external-cavity surface-emitting laser. <i>Optics Express</i> , 2019 , 27, 11914-11929	3.3	12
113	Bragg grating cavities embedded into nano-photonic waveguides for Purcell enhanced quantum dot emission. <i>Optics Express</i> , 2018 , 26, 30614-30622	3.3	11
112	Chem/bio sensing with non-classical light and integrated photonics. <i>Analyst, The</i> , 2018 , 143, 593-605	5	11
111	Spectrally and time-resolved cathodoluminescence microscopy of semipolar InGa _{1-x} N SQW on (11 $\bar{1}$ 2) and (10 $\bar{1}$ 1) pyramid facets. <i>Physica Status Solidi (B): Basic Research</i> , 2011 , 248, 632-637	1.3	10
110	Laterally Coupled InGa _x N/GaN DFB Laser Diodes. <i>Physica Status Solidi A</i> , 2002 , 192, 301-307		10
109	Overcoming correlation fluctuations in two-photon interference experiments with differently bright and independently blinking remote quantum emitters. <i>Physical Review B</i> , 2018 , 97,	3.3	10
108	Optical Gain and Lasing Properties of InP/AlGaInP Quantum-Dot Laser Diode Emitting at 660 nm. <i>IEEE Journal of Quantum Electronics</i> , 2019 , 55, 1-7	2	9
107	Strong antibunching from electrically driven devices with long pulses: A regime for quantum-dot single-photon generation. <i>Physical Review B</i> , 2012 , 86,	3.3	9
106	Single-photon emission from electrically driven InP quantum dots epitaxially grown on CMOS-compatible Si(001). <i>Nanotechnology</i> , 2012 , 23, 335201	3.4	9
105	Strong mode coupling in InP quantum dot-based GaInP microdisk cavity dimers. <i>New Journal of Physics</i> , 2013 , 15, 013060	2.9	9
104	Quaternary Al _x In _y Ga _{1-x-y} N layers deposited by pulsed metal-organic vapor-phase epitaxy for high efficiency light emission. <i>Journal of Crystal Growth</i> , 2011 , 315, 254-257	1.6	9
103	Electron and hole spins in InP/(Ga,In)P self-assembled quantum dots. <i>Physical Review B</i> , 2012 , 86,	3.3	9
102	Vertical asymmetric double quantum dots. <i>Journal of Crystal Growth</i> , 2007 , 298, 603-606	1.6	9
101	Pure single-photon emission from In(Ga)As QDs in a tunable fiber-based external mirror microcavity. <i>Quantum Science and Technology</i> , 2018 , 3, 034009	5.5	9
100	Strain compensation techniques for red AlGaInP-VECSELs: Performance comparison of epitaxial designs. <i>Journal of Crystal Growth</i> , 2013 , 370, 208-211	1.6	8
99	Vertically stacked and laterally ordered InP and In(Ga)As quantum dots for quantum gate applications. <i>Physica Status Solidi (B): Basic Research</i> , 2012 , 249, 737-746	1.3	8

98	Transverse-Mode Analysis of Red-Emitting Highly Polarized Vertical-Cavity Surface-Emitting Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011 , 17, 724-729	3.8	8
97	Investigations on local Ga and In incorporation of GaInN quantum wells on facets of selectively grown GaN stripes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1587-1590		8
96	Evidence of different confinement regimes in site-controlled pyramidal InGaN structures. <i>Physica Status Solidi (B): Basic Research</i> , 2005 , 242, R97-R99	1.3	8
95	Characterization of a Photon-Number Resolving SNSPD Using Poissonian and Sub-Poissonian Light. <i>IEEE Transactions on Applied Superconductivity</i> , 2019 , 29, 1-5	1.8	7
94	Excited-state spectroscopy of single lateral self-assembled InGaAs quantum dot molecules. <i>Physical Review B</i> , 2012 , 85,	3.3	7
93	Bright Purcell Enhanced Single-Photon Source in the Telecom O-Band Based on a Quantum Dot in a Circular Bragg Grating. <i>Nano Letters</i> , 2021 , 21, 7740-7745	11.5	7
92	Self-mode-locked AlGaInP-VECSEL. <i>Applied Physics Letters</i> , 2017 , 111, 182105	3.4	6
91	Comparison of AlGaInP-VECSEL gain structures. <i>Journal of Crystal Growth</i> , 2015 , 414, 219-222	1.6	6
90	Pulsed single-photon resonant-cavity quantum dot LED. <i>Journal of Crystal Growth</i> , 2011 , 315, 127-130	1.6	6
89	Time-resolved and single dot spectroscopy of type II InP/GaInP quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 1197-1200		6
88	Selective growth of GaInN quantum dot structures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005 , 26, 133-137	3	6
87	Quantum dot-based broadband optical antenna for efficient extraction of single photons in the telecom O-band. <i>Optics Express</i> , 2020 , 28, 19457-19468	3.3	6
86	Tuning emission energy and fine structure splitting in quantum dots emitting in the telecom O-band. <i>AIP Advances</i> , 2019 , 9, 085112	1.5	5
85	Signatures of single-photon interaction between two quantum dots located in different cavities of a weakly coupled double microdisk structure. <i>Physical Review B</i> , 2018 , 97,	3.3	5
84	Optical investigations on single vertically coupled InP/GaInP quantum dot pairs. <i>Physica Status Solidi (B): Basic Research</i> , 2012 , 249, 747-751	1.3	5
83	Optical properties of red emitting self-assembled InP/(Al _{0.20} Ga _{0.80}) _{0.51} In _{0.49} P quantum dot based micropillars. <i>Optics Express</i> , 2010 , 18, 12543-51	3.3	5
82	The phase boundary of superconducting niobium thin films with antidot arrays fabricated with microsphere photolithography. <i>Superconductor Science and Technology</i> , 2012 , 25, 065020	3.1	5
81	Optical studies of GaInP/GaP quantum dots. <i>Journal of Luminescence</i> , 2003 , 102-103, 1-6	3.8	5

80	Purcell-enhanced single-photon emission from a strain-tunable quantum dot in a cavity-waveguide device. <i>Applied Physics Letters</i> , 2020 , 117, 254002	3-4	5
79	3D printed micro-optics for quantum technology: Optimised coupling of single quantum dot emission into a single-mode fibre. <i>Light Advanced Manufacturing</i> , 2021 , 2, 1-17	1	5
78	Single-photon light-emitting diodes based on preselected quantum dots using a deterministic lithography technique. <i>Applied Physics Letters</i> , 2019 , 114, 222101	3-4	4
77	Characterization of spectral diffusion by slow-light photon-correlation spectroscopy. <i>Physical Review B</i> , 2020 , 101,	3-3	4
76	Red AlGaInP-VECSEL emitting at around 665 nm: strain compensation and performance comparison of different epitaxial designs 2012 ,		4
75	Site-controlled growth of InP/GaInP islands on periodic hole patterns in GaAs substrates produced by microsphere photolithography. <i>Journal of Crystal Growth</i> , 2013 , 370, 146-149	1.6	4
74	InP quantum dots for applications in laser devices and future solid-state quantum gates. <i>Journal of Physics: Conference Series</i> , 2010 , 245, 012077	0.3	4
73	Transport of laser accelerated proton beams and isochoric heating of matter. <i>Journal of Physics: Conference Series</i> , 2010 , 244, 012009	0.3	4
72	Red to orange electroluminescence from InP/AlGaInP quantum dots at room temperature. <i>Journal of Crystal Growth</i> , 2008 , 310, 5098-5101	1.6	4
71	Increased single-photon emission from InP/AlGaInP quantum dots grown on AlGaAs distributed Bragg reflectors. <i>Journal of Crystal Growth</i> , 2008 , 310, 4818-4820	1.6	4
70	In-Redistribution in a GaInN Quantum Well upon Thermal Annealing. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 234, 738-741	1.3	4
69	Initial Experiments to Obtain Self-Assembled GaInN Quantum Islands by MOVPE. <i>Physica Status Solidi A</i> , 2002 , 192, 412-416		4
68	160°C pulsed laser operation of AlGaInP-based vertical-cavity surface-emitting lasers. <i>Electronics Letters</i> , 2003 , 39, 1654	1.1	4
67	Quantum dot based mode-locked AlGaInP-VECSEL 2015 ,		3
66	Semiconductor Quantum Dots for Integrated Quantum Photonics (Adv. Quantum Technol. 9/2019). <i>Advanced Quantum Technologies</i> , 2019 , 2, 1970053	4-3	3
65	Active and Passive LC Based Polarization Elements. <i>Molecular Crystals and Liquid Crystals</i> , 2014 , 594, 140-149	0.5	3
64	Influence of the oxide aperture radius on the mode spectra of (Al,Ga)As vertical microcavities with electrically excited InP quantum dots. <i>Applied Physics Letters</i> , 2013 , 102, 011132	3-4	3
63	Growth and characterization of electrically pumped red-emitting VCSEL with embedded InP/AlGaInP quantumdots. <i>Journal of Crystal Growth</i> , 2011 , 315, 131-133	1.6	3

62	MOVPE grown quaternary AlInGaN layers for polarization matched quantum wells and efficient active regions. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2163-2166		3
61	Regions of Different Confinement in Low-Dimensional AlyInxGa1-x-yN Quantum Structures. <i>Advances in OptoElectronics</i> , 2007 , 2007, 1-6	0.5	3
60	Optical studies of GaIn1-xP/Ga0.5In0.5P quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 1225-1228		3
59	Realization of a tunable fiber-based double cavity system. <i>Physical Review B</i> , 2020 , 102,	3.3	3
58	Resonance fluorescence of single In(Ga)As quantum dots emitting in the telecom C-band. <i>Applied Physics Letters</i> , 2021 , 118, 244002	3.4	3
57	Stable fundamental and dual-pulse mode locking of red-emitting VECSELS. <i>Laser Physics Letters</i> , 2020 , 17, 065001	1.5	2
56	Efficiency and power scaling of in-well and multi-pass pumped AlGaInP VECSELS 2016 ,		2
55	Gain chip design, power scaling and intra-cavity frequency doubling with LBO of optically pumped red-emitting AlGaInP-VECSELS 2016 ,		2
54	Femtosecond mode-locked red AlGaInP-VECSEL 2014 ,		2
53	Wavelength tunable red AlGaInP-VECSEL emitting at around 660 nm 2011 ,		2
52	Spectral features in different sized InGaN/GaN micropylamids. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2387-2389		2
51	InP quantum dots in pillar microcavities I mode spectra and single-photon emission. <i>Journal of Physics: Conference Series</i> , 2010 , 210, 012010	0.3	2
50	InP-quantum dots in Al0.20Ga0.80InP with different barrier configurations. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 906-909		2
49	Frequency doubled AlGaInP-VECSEL with high output power at 331 nm and a large wavelength tuning range in the UV 2012 ,		2
48	Pulsed layer growth of AlInGaN nanostructures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 1491-1494		2
47	Non-resonant tunneling in single pairs of vertically stacked asymmetric InP/GaInP quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008 , 40, 1958-1960	3	2
46	Structural and optical characterization of Aly Inx Ga1-x-y N quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 2073-2077		2
45	Growth of self-assembled AlxInyGa1-x-yN quantum dots by MOVPE. <i>Journal of Crystal Growth</i> , 2004 , 272, 186-191	1.6	2

44	Photoluminescence Studies on InGaN/GaN Quantum Dots. <i>Physica Status Solidi A</i> , 2002 , 192, 91-96		2
43	Controllable Delay and Polarization Routing of Single Photons. <i>Advanced Quantum Technologies</i> , 2020 , 3, 1900057	4-3	2
42	Wavelength and Pump-Power Dependent Nonlinear Refraction and Absorption in a Semiconductor Disk Laser. <i>IEEE Photonics Technology Letters</i> , 2020 , 32, 85-88	2.2	2
41	The optically pumped semiconductor membrane external-cavity surface-emitting laser (MECSEL): a concept based on a diamond-sandwiched active region 2017 ,		1
40	Fabrication and optical characterization of large scale membrane containing InP/AlGaInP quantum dots. <i>Nanotechnology</i> , 2015 , 26, 235201	3-4	1
39	Epitaxially Grown Indium Phosphide Quantum Dots on a Virtual Ge Substrate Realized on Si(001). <i>Applied Physics Express</i> , 2012 , 5, 042001	2.4	1
38	Low threshold electrically pumped red emitting InP/Al _{0.20} GaInP quantum dot vertical microcavity laser 2009 ,		1
37	Generation of UV laser light via intra-cavity frequency doubling of an AlGaInP-VECSEL 2011 ,		1
36	Transverse mode and polarization characteristics of AlGaInP-based VCSELs with integrated multiple oxide apertures 2012 ,		1
35	UV laser emission around 330 nm via intracavity frequency doubling of a tunable red AlGaInP-VECSEL 2012 ,		1
34	Direct imaging of GaN Pyramids covered by InGaN Single Quantum Well using nano-scale Scanning Transmission Electron Microscopy Cathodoluminescence. <i>Microscopy and Microanalysis</i> , 2012 , 18, 1838-1839	10-5	1
33	DC and pulsed electrical excitation of single quantum dots 2010 ,		1
32	Growth of red InP/GaInP quantum dots on a low density InAs/GaAs island seed layer by MOVPE. <i>Journal of Crystal Growth</i> , 2008 , 310, 5089-5092	1.6	1
31	Analog Modulation of 650-nm VCSELs. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 583-585	2.2	1
30	Carrier dynamics in site-controlled Ga _{1-x} In _x N quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 2060-2064		1
29	Study of as deposited metal contacts for n-SiC. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004 , 1, 2533-2536		1
28	Red VCSEL for automotive applications 2005 ,		1
27	Optical investigations on InP and GaInP quantum dots		1

26	Optical charge injection and coherent control of a quantum-dot spin-qubit emitting at telecom wavelengths.. <i>Nature Communications</i> , 2022 , 13, 748	17.4	1
25	Single-photon and polarization-entangled photon emission from InAs quantum dots in the telecom C-band 2018 ,		1
24	Gaussian-like transverse-mode profile characteristics of high-power large-area red-emitting VCSELs. <i>Optics Letters</i> , 2020 , 45, 1419-1422	3	1
23	Achieving stable fiber coupling of quantum dot telecom C-band single-photons to an SOI photonic device. <i>Applied Physics Letters</i> , 2021 , 119, 211101	3.4	1
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